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annealing temperature. When the annealing process is conducted at 350°, the H2 gas is supplied with a flow-rate of 400 SCCM. It should be noted that the order of the foregoing steps S6 and S7 my be exchanged.

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Next, in the step of FIG.16 corresponding to the step S16 of FIG.10, the structure of FIG.15 is subjected to an annealing process conducted in a gas atmosphere. In the step of FIG.16, an H_2 gas or an N_2 gas is used for the annealing atmosphere and the annealing is conducted under a reduced pressure of at least 10 Pa, preferably 670 Pa, at a temperature of 300-350°C over a duration of about 5 minutes while supplying the reducing gas with a flow-rate of 400 SCCM. It should be noted that the duration of the annealing process depends on the annealing temperature.

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See the attached Appendix for the changes made to effect the above paragraph

IN THE CLAIMS:

Please amend claims 1, 4, 5 and 11 to read as follows:

1. (Amended) A method for fabrication a semiconductor device, comprising the steps of:

forming a barrier conductor layer on a substrate;

exposing said barrier conductor layer to a first gas atmosphere containing a reducing gas at an elevated substrate temperature;

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forming, after said step of exposing said barrier conductor layer to said first gas atmosphere, a metal film on said barrier conductor layer by a CVD process; and